

REVISIONS

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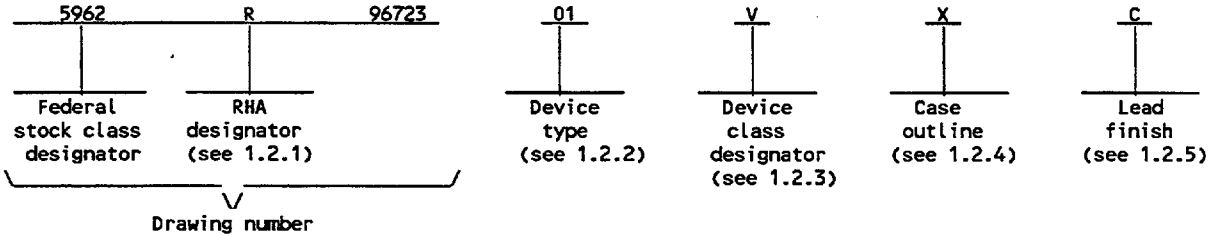
REV STATUS OF SHEETS	REV																			
	SHEET	1	2	3	4	5	6	7	8	9	10	11								

PMIC N/A	PREPARED BY Sandra Rooney	DEFENSE ELECTRONICS SUPPLY CENTER DAYTON, OHIO 45444		
<p align="center">STANDARD MICROCIRCUIT DRAWING</p> <p>THIS DRAWING IS AVAILABLE FOR USE BY ALL DEPARTMENTS AND AGENCIES OF THE DEPARTMENT OF DEFENSE</p> <p>AMSC N/A</p>	CHECKED BY Sandra Rooney	MICROCIRCUIT, LINEAR, RADIATION HARDENED, TRIPLE LINE RECEIVERS, MONOLITHIC SILICON		
	APPROVED BY Michael A. Frye			
	DRAWING APPROVAL DATE 95-11-20	SIZE A	CAGE CODE 67268	5962-96723
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1. SCOPE

1.1 Scope. This drawing forms a part of a one part - one part number documentation system (see 6.6 herein). Two product assurance classes consisting of military high reliability (device classes Q and M) and space application (device class V), and a choice of case outlines and lead finishes are available and are reflected in the Part or Identifying Number (PIN). Device class M microcircuits represent non-JAN class B microcircuits in accordance with 1.2.1 of MIL-STD-883, "Provisions for the use of MIL-STD-883 in conjunction with compliant non-JAN devices". When available, a choice of Radiation Hardness Assurance (RHA) Levels are reflected in the PIN.

1.2 PIN. The PIN shall be as shown in the following example:



1.2.1 RHA designator. Device class M RHA marked devices shall meet the MIL-I-38535 appendix A specified RHA levels and shall be marked with the appropriate RHA designator. Device classes Q and V RHA marked devices shall meet the MIL-I-38535 specified RHA levels and shall be marked with the appropriate RHA designator. A dash (-) indicates a non-RHA device.

1.2.2 Device type(s). The device type(s) shall identify the circuit function as follows:

Device type	Generic number	Circuit function
01	HS-246RH	Radiation hardened DI triple line receiver
02	HS-248RH	Radiation hardened DI triple party-line receiver

1.2.3 Device class designator. The device class designator shall be a single letter identifying the product assurance level as follows:

Device class	Device requirements documentation
M	Vendor self-certification to the requirements for non-JAN class B microcircuits in accordance with 1.2.1 of MIL-STD-883
Q or V	Certification and qualification to MIL-I-38535

1.2.4 Case outline(s). The case outline(s) shall be as designated in MIL-STD-1835 and as follows:

Outline letter	Descriptive designator	Terminals	Package style
C	CDIP2-T14	14	Dual-in-line
X	CDFP3-F14	14	Flat package

1.2.5 Lead finish. The lead finish shall be as specified in MIL-STD-883 (see 3.1 herein) for class M or MIL-I-38535 for classes Q and V. Finish letter "X" shall not be marked on the microcircuit or its packaging. The "X" designation is for use in specifications when lead finishes A, B, and C are considered acceptable and interchangeable without preference.

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1.3 Absolute maximum ratings. 1/

Supply voltage (V_{CC})	- - - - -	-0.5 V dc to +8.0 V dc
Supply voltage (V_{EE})	- - - - -	-8.0 V dc to +0.5 V dc
Output voltage	- - - - -	-0.5 V dc to +6.0 V dc
Input voltage	- - - - -	-1.0 V dc to +1.0 V dc
Input current	- - - - -	-25 mA to +25 mA
Output current	- - - - -	50 mA
Storage temperature range	- - - - -	-65°C to +150°C
Maximum package power dissipation at $T_A = +125^\circ\text{C}$ (P_D):		
Case outline C	- - - - -	0.68 W 2/
Case outline X	- - - - -	0.43 W 2/
Thermal resistance, junction-to-case (θ_{JC}):		
Case outline C	- - - - -	24°C/W
Case outline X	- - - - -	30°C/W
Thermal resistance, junction-to-ambient (θ_{JA}):		
Case outline C	- - - - -	74°C/W
Case outline X	- - - - -	116°C/W
Lead temperature (soldering, 10 seconds)	- - - - -	+275°C
Junction temperature (T_J)	- - - - -	+175°C

1.4 Recommended operating conditions.

Operating voltage range	- - - - -	+4.5 V dc to +5.5 V dc
Ambient operating temperature range (T_A)	- - - - -	-55°C to +125°C
Radiation features:		
Dose rate upset	- - - - -	1x10 ⁹ Rads (SI)/s
Total dose	- - - - -	2x10 ⁵ Rads (Si)
Dose rate latch-up 3/	- - - - -	None
Neutron	- - - - -	5x10 ¹² N/cm ²

2. APPLICABLE DOCUMENTS

2.1 Government specification, standards, bulletin, and handbook. Unless otherwise specified, the following specification, standards, bulletin, and handbook of the issue listed in that issue of the Department of Defense Index of Specifications and Standards specified in the solicitation, form a part of this drawing to the extent specified herein.

SPECIFICATION

MILITARY

MIL-I-38535 - Integrated Circuits, Manufacturing, General Specification for.

STANDARDS

MILITARY

- MIL-STD-883 - Test Methods and Procedures for Microelectronics.
- MIL-STD-973 - Configuration Management.
- MIL-STD-1835 - Microcircuit Case Outlines.

BULLETIN

MILITARY

MIL-BUL-103 - List of Standard Microcircuit Drawings (SMD's).

- 1/ Stresses above the absolute maximum rating may cause permanent damage to the device. Extended operation at the maximum levels may degrade performance and affect reliability.
- 2/ If device power exceeds package dissipation capacity, provide heat sinking or derate linearly (the derating is based on θ_{JA}) at the following rates:

Case outline C	- - - - -	13.5 mW/°C
Case outline X	- - - - -	8.6 mW/°C
- 3/ Guaranteed by process or design, not tested.

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HANDBOOK

MILITARY

MIL-HDBK-780 - Standardized Military Drawings.

(Copies of the specification, standards, bulletin, and handbook required by manufacturers in connection with specific acquisition functions should be obtained from the contracting activity or as directed by the contracting activity.)

2.2 Order of precedence. In the event of a conflict between the text of this drawing and the references cited herein, the text of this drawing shall take precedence.

3. REQUIREMENTS

3.1 Item requirements. The individual item requirements for device class M shall be in accordance with 1.2.1 of MIL-STD-883, "Provisions for the use of MIL-STD-883 in conjunction with compliant non-JAN devices" and as specified herein. The individual item requirements for device classes Q and V shall be in accordance with MIL-I-38535 and as specified herein or as modified in the device manufacturer's Quality Management (QM) plan. The modification in the QM plan shall not effect the form, fit, or function as described herein.

3.2 Design, construction, and physical dimensions. The design, construction, and physical dimensions shall be as specified in MIL-STD-883 (see 3.1 herein) for device class M and MIL-I-38535 for device classes Q and V and herein.

3.2.1 Case outline(s). The case outline(s) shall be in accordance with 1.2.4 herein.

3.2.2 Terminal connections. The terminal connections shall be as specified on figure 1.

3.2.3 Load circuit and switching waveform. The load circuit and switching waveform shall be as specified on figure 2.

3.2.4 Radiation exposure circuit. The radiation exposure circuit shall be as specified in table III.

3.3 Electrical performance characteristics and postirradiation parameter limits. Unless otherwise specified herein, the electrical performance characteristics and post irradiation parameter limits are as specified in table I and shall apply over the full ambient operating temperature range.

3.4 Electrical test requirements. The electrical test requirements shall be the subgroups specified in table IIA. The electrical tests for each subgroup are defined in table I.

3.5 Marking. The part shall be marked with the PIN listed in 1.2 herein. Marking for device class M shall be in accordance with MIL-STD-883 (see 3.1 herein). In addition, the manufacturer's PIN may also be marked as listed in MIL-BUL-103. Marking for device classes Q and V shall be in accordance with MIL-I-38535.

3.5.1 Certification/compliance mark. The compliance mark for device class M shall be a "C" as required in MIL-STD-883 (see 3.1 herein). The certification mark for device classes Q and V shall be a "QML" or "Q" as required in MIL-I-38535.

3.6 Certificate of compliance. For device class M, a certificate of compliance shall be required from a manufacturer in order to be listed as an approved source of supply in MIL-BUL-103 (see 6.7.2 herein). For device classes Q and V, a certificate of compliance shall be required from a QML-38535 listed manufacturer in order to supply to the requirements of this drawing (see 6.7.1 herein). The certificate of compliance submitted to DESC-EC prior to listing as an approved source of supply for this drawing shall affirm that the manufacturer's product meets, for device class M, the requirements of MIL-STD-883 (see 3.1 herein), or for device classes Q and V, the requirements of MIL-I-38535 and the requirements herein.

3.7 Certificate of conformance. A certificate of conformance as required for device class M in MIL-STD-883 (see 3.1 herein) or for device classes Q and V in MIL-I-38535 shall be provided with each lot of microcircuits delivered to this drawing.

3.8 Notification of change for device class M. For device class M, notification to DESC-EC of change of product (see 6.2 herein) involving devices acquired to this drawing is required for any change as defined in MIL-STD-973.

3.9 Verification and review for device class M. For device class M, DESC, DESC's agent, and the acquiring activity retain the option to review the manufacturer's facility and applicable required documentation. Offshore documentation shall be made available onshore at the option of the reviewer.

3.10 Microcircuit group assignment for device class M. Device class M devices covered by this drawing shall be in microcircuit group number 53 (see MIL-I-38535, appendix A).

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TABLE I. Electrical performance characteristics.

Test	Symbol	Conditions ^{1/} -55°C ≤ T _A ≤ +125°C unless otherwise specified	Device type	Group A subgroups	Limits		Unit
					Min	Max	
Input resistance	R _{IN}	V _{CC} = 5.0 V, V _{EE} = -5.0 V	01	1, 2, 3	39	90	Ω
Pullup resistance	R _{PU}	V _{CC} = 5.0 V, V _{EE} = -5.0 V	02	1, 2, 3	4.1	10.5	kΩ
Logical "1" output voltage	V _{OH}	V _{CC} = 4.5 V, V _{EE} = -4.5 V, I _{OH} = -120 mA ^{2/}	02	1, 2, 3	2.5		V
Logical "0" output voltage	V _{OL}	V _{CC} = 4.5 V, V _{EE} = -4.5 V, I _{OH} = 10 mA ^{3/}	01	1, 2, 3		0.45	V
		V _{CC} = 4.5 V, V _{EE} = -4.5 V, I _{OH} = 9.6 mA ^{3/}	02			0.45	
Logical "0" output voltage, input short circuit	V _{OLSC}	V _{CC} = 4.5 V, V _{EE} = -4.5 V, I _{OL} = 3.2 mA ^{4/}	01,02	1		0.45	V
Power supply current	I _{CC}	V _{CC} = 5.5 V, V _{EE} = -5.5 V ^{5/ 6/}	01	1		6.6	mA
		V _{CC} = 5.5 V, V _{EE} = -5.5 V ^{5/ 6/}	02			7.8	
Power supply current	I _{EE}	V _{CC} = 5.5 V, V _{EE} = -5.5 V ^{5/ 6/}	01,02	1		6.0	
Propagation delay	T _{PLH}	V _{CC} = 4.5 V, V _{EE} = -4.5 V See figure 2	01,02	9, 10, 11		30	ns
	T _{PHL}						

^{1/} Devices supplied to this drawing will meet all levels M, D, L, R of irradiation. However, this device is only tested at the 'R' level. When performing post irradiation measurements for any RHA level, T_A = +25°C.

^{2/} (+)I_{IN} = 1.5 mA; (-)Input = Open. For device type 02, use external 50 Ω resistor or (+)I_{IN} = 0.75 mA. See figure 2.

^{3/} (+)Input = Open; (-)I_{IN} = 1.5 mA. For device type 02, use external 50 Ω resistor or (-)I_{IN} = 0.75 mA. See figure 2.

^{4/} Both inputs shorted to GND; or both inputs open such that 50 Ω termination resistors are in the circuit.

^{5/} (+)Input = Open; (-)I_{IN} = 3 mA.

^{6/} (+)I_{IN} = 3 mA; (-)Input = Open.

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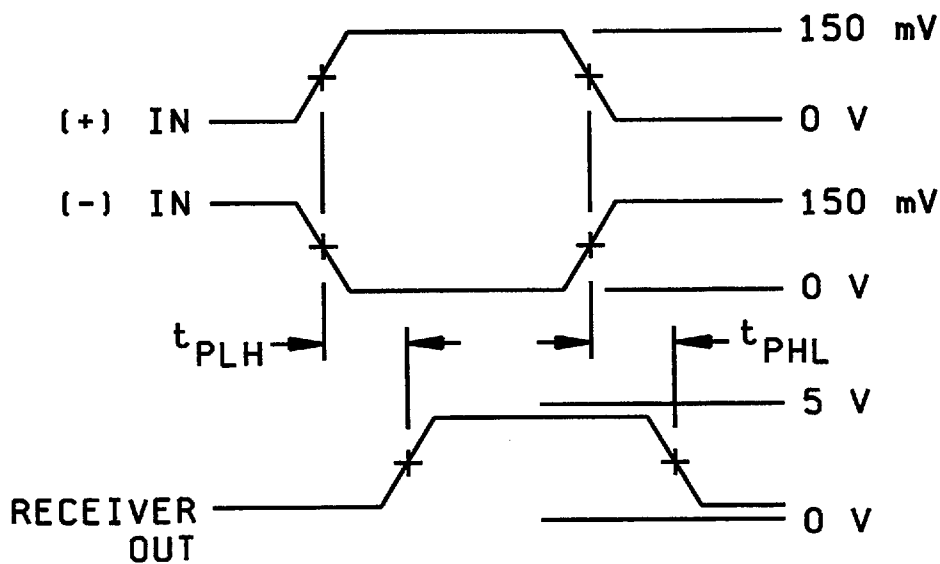
Device types	01 and 02
Case outlines	C and X
Terminal number	Terminal symbol
1	(-)INPUT 1
2	(+)INPUT 1
3	(R1)OUTPUT 1
4	(-)INPUT 2
5	(+)INPUT 2
6	(R2)OUTPUT 2
7	GND
8	(-)INPUT 3
9	(+)INPUT 3
10	(R3)OUTPUT 3
11	(R3)V _{EE}
12	(R1 & R2)V _{EE}
13	(R3)V _{CC}
14	(R1 & R2)V _{CC}

FIGURE 1. Terminal connections.

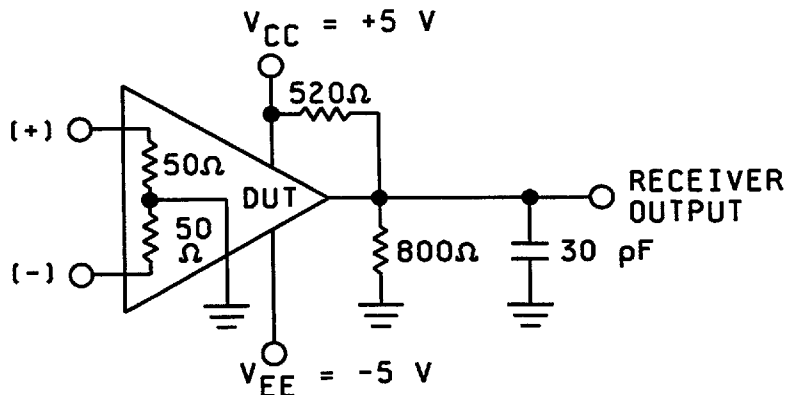
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9004708 0015812 T35



NOTES:
 Input: $T_{TLH} \leq 10 \text{ ns}$
 $T_{THL} \leq 10 \text{ ns}$
 $p_w = 500 \text{ ns}$
 $f = 1 \text{ MHz}$



NOTE: External 50 Ω resistors needed for device type 02.

FIGURE 2. Load circuit and switching waveform.

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TABLE IIA. Electrical test requirements.

Test requirements	Subgroups (in accordance with MIL-STD-883, TM 5005, table I)	Subgroups (in accordance with MIL-I-38535, table III)	
	Device class M	Device class Q	Device class V
Interim electrical parameters (see 4.2)	1	1	1
Final electrical parameters (see 4.2)	1, 2, 3, 1/ 9, 10, 11	1, 2, 3, 1/ 9, 10, 11	1, 2, 3, 1/ 2/ 9, 10, 11, Δ
Group A test requirements (see 4.4)	1, 2, 3, 9, 10, 11	1, 2, 3, 9, 10, 11	1, 2, 3, 9, 10, 11
Group C end-point electrical parameters (see 4.4)	1, 2, 3, 9	1, 2, 3, 9	1, 2, 3, 2/ 9, 10, 11
Group D end-point electrical parameters (see 4.4)	1	1	1
Group E end-point electrical parameters (see 4.4)	1	1	1

1/ PDA applies to subgroup 1. For class Q and V to subgroups 1 and Δ.

2/ Delta limits (see table IIB) shall be required and the delta values shall be computed with reference to the zero hour electrical parameters (see table I).

4. QUALITY ASSURANCE PROVISIONS

4.1 Sampling and inspection. For device class M, sampling and inspection procedures shall be in accordance with MIL-STD-883 (see 3.1 herein). For device classes Q and V, sampling and inspection procedures shall be in accordance with MIL-I-38535 or as modified in the device manufacturer's Quality Management (QM) plan. The modification in the QM plan shall not effect the form, fit, or function as described herein.

4.2 Screening. For device class M, screening shall be in accordance with method 5004 of MIL-STD-883, and shall be conducted on all devices prior to quality conformance inspection. For device classes Q and V, screening shall be in accordance with MIL-I-38535, and shall be conducted on all devices prior to qualification and technology conformance inspection.

4.2.1 Additional criteria for device class M.

a. Burn-in test, method 1015 of MIL-STD-883.

(1) Test condition A, B, C, or D. The test circuit shall be maintained by the manufacturer under document revision level control and shall be made available to the preparing or acquiring activity upon request. The test circuit shall specify the inputs, outputs, biases, and power dissipation, as applicable, in accordance with the intent specified in test method 1015.

(2) $T_A = +125^\circ\text{C}$, minimum.

b. Interim and final electrical test parameters shall be as specified in table IIA herein.

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TABLE IIB. Burn-in delta parameters and group C delta parameters (+25°C).

PARAMETER	SYMBOL	DELTA LIMITS
Low level output voltage	V_{OL}	± 90 mV
High level output voltage	V_{OH}	± 500 mV
Power supply current	I_{CC}	± 2 mA
Power supply current	I_{EE}	± 2 mA

TABLE III. Irradiation test connections. $T_A = +25^\circ\text{C} \pm 5^\circ\text{C}$

-0.1 V	+0.1 V	NC	GND	+5.5 \pm 0.5 V	-5.5 V \pm 0.5 V
1, 4, 8	2, 5, 9	3, 6, 10	7	13, 14	11, 12

4.2.2 Additional criteria for device classes Q and V.

- a. The burn-in test duration, test condition and test temperature, or approved alternatives shall be as specified in the device manufacturer's QM plan in accordance with MIL-I-38535. The burn-in test circuit shall be maintained under document revision level control of the device manufacturer's Technology Review Board (TRB) in accordance with MIL-I-38535 and shall be made available to the acquiring or preparing activity upon request. The test circuit shall specify the inputs, outputs, biases, and power dissipation, as applicable, in accordance with the intent specified in test method 1015.
- b. Interim and final electrical test parameters shall be as specified in table IIA herein.
- c. Additional screening for device class V beyond the requirements of device class Q shall be as specified in appendix B of MIL-I-38535 or as modified in the device manufacturer's Quality Management (QM) plan.

4.3 Qualification inspection for device classes Q and V. Qualification inspection for device classes Q and V shall be in accordance with MIL-I-38535. Inspections to be performed shall be those specified in MIL-I-38535 and herein for groups A, B, C, D, and E inspections (see 4.4.1 through 4.4.4).

4.4 Conformance inspection. Quality conformance inspection for device class M shall be in accordance with MIL-STD-883 (see 3.1 herein) and as specified herein. Inspections to be performed for device class M shall be those specified in method 5005 of MIL-STD-883 and herein for groups A, B, C, D, and E inspections (see 4.4.1 through 4.4.4). Technology conformance inspection for classes Q and V shall be in accordance with MIL-I-38535 or as specified in QM plan including groups A, B, C, D, and E inspections and as specified herein except where option 2 of MIL-I-38535 permits alternate in-line control testing.

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4.4.1 Group A inspection.

- a. Tests shall be as specified in table IIA herein.
- b. Subgroups 4, 5, 6, 7, and 8 in table I, method 5005 of MIL-STD-883 shall be omitted.

4.4.2 Group C inspection. The group C inspection end-point electrical parameters shall be as specified in table IIA herein.

4.4.2.1 Additional criteria for device class M. Steady-state life test conditions, method 1005 of MIL-STD-883:

- a. Test condition A, B, C, or D. The test circuit shall be maintained by the manufacturer under document revision level control and shall be made available to the preparing or acquiring activity upon request. The test circuit shall specify the inputs, outputs, biases, and power dissipation, as applicable, in accordance with the intent specified in test method 1005.
- b. $T_A = +125^\circ\text{C}$, minimum.
- c. Test duration: 1,000 hours, except as permitted by method 1005 of MIL-STD-883.

4.4.2.2 Additional criteria for device classes Q and V. The steady-state life test duration, test condition and test temperature, or approved alternatives shall be as specified in the device manufacturer's QM plan in accordance with MIL-I-38535. The test circuit shall be maintained under document revision level control by the device manufacturer's TRB, in accordance with MIL-I-38535, and shall be made available to the acquiring or preparing activity upon request. The test circuit shall specify the inputs, outputs, biases, and power dissipation, as applicable, in accordance with the intent specified in test method 1005.

4.4.3 Group D inspection. The group D inspection end-point electrical parameters shall be as specified in table IIA herein.

4.4.4 Group E inspection. Group E inspection is required only for parts intended to be marked as radiation hardness assured (see 3.5 herein). RHA levels for device classes M, Q and V shall be as specified in MIL-I-38535. End-point electrical parameters shall be as specified in table IIA herein.

4.4.4.1 Total dose irradiation testing. Total dose irradiation testing shall be performed in accordance with MIL-STD-883 method 1019 and as specified herein.

4.4.4.1.1 Accelerated aging test. Accelerated aging tests shall be performed on all devices requiring a RHA level greater than 5k rads(Si). The post-anneal end-point electrical parameter limits shall be as specified in table I herein and shall be the pre-irradiation end-point electrical parameter limit at $25^\circ\text{C} \pm 5^\circ\text{C}$. Testing shall be performed at initial qualification and after any design or process changes which may affect the RHA response of the device.

4.4.4.2 Dose rate induced latchup testing. Dose rate induced latchup testing shall be performed in accordance with test method 1020 of MIL-STD-883 and as specified herein (See 1.4). Tests shall be performed on devices, SEC, or approved test structures at technology qualification and after any design or process changes which may effect the RHA capability of the process.

4.4.4.3 Dose rate upset testing. Dose rate upset testing shall be performed in accordance with test method 1023 of MIL-STD-883 and herein (See 1.4).

- a. Transient dose rate upset testing shall be performed at initial qualification and after any design or process changes which may effect the RHA performance of the devices. Test 10 devices with 0 defects unless otherwise specified.
- b. Transient dose rate upset testing for class Q and V devices shall be performed as specified by a TRB approved radiation hardness assurance plan and MIL-I-38535.

4.4.4.4 Dose rate burnout. When required by the customer, test shall be performed on devices, SEC, or approved test structures at technology qualifications and after any design or process changes which may effect the RHA capability of the process. Dose rate burnout shall be performed in accordance with test method 1023 of MIL-STD-883 and as specified herein.

5. PACKAGING

5.1 Packaging requirements. The requirements for packaging shall be in accordance with MIL-STD-883 (see 3.1 herein) for device class M and MIL-I-38535 for device classes Q and V.

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6. NOTES

6.1 Intended use. Microcircuits conforming to this drawing are intended for use for Government microcircuit applications (original equipment), design applications, and logistics purposes.

6.1.1 Replaceability. Microcircuits covered by this drawing will replace the same generic device covered by a contractor-prepared specification or drawing.

6.1.2 Substitutability. Device class Q devices will replace device class M devices.

6.2 Configuration control of SMD's. All proposed changes to existing SMD's will be coordinated with the users of record for the individual documents. This coordination will be accomplished in accordance with MIL-STD-973 using DD Form 1692, Engineering Change Proposal.

6.3 Record of users. Military and industrial users shall inform Defense Electronics Supply Center when a system application requires configuration control and which SMD's are applicable to that system. DESC will maintain a record of users and this list will be used for coordination and distribution of changes to the drawings. Users of drawings covering microelectronic devices (FSC 5962) should contact DESC-EC, telephone (513) 296-6047.

6.4 Comments. Comments on this drawing should be directed to DESC-EC, Dayton, Ohio 45444-5270, or telephone (513) 296-5377.

6.5 Abbreviations, symbols, and definitions. The abbreviations, symbols, and definitions used herein are defined in MIL-I-38535 and MIL-STD-1331.

6.6 One part - one part number system. The one part - one part number system described below has been developed to allow for transitions between identical generic devices covered by the three major microcircuit requirements documents (MIL-H-38534, MIL-I-38535, and 1.2.1 of MIL-STD-883) without the necessity for the generation of unique PIN's. The three military requirements documents represent different class levels, and previously when a device manufacturer upgraded military product from one class level to another, the benefits of the upgraded product were unavailable to the Original Equipment Manufacturer (OEM), that was contractually locked into the original unique PIN. By establishing a one part number system covering all three documents, the OEM can acquire to the highest class level available for a given generic device to meet system needs without modifying the original contract parts selection criteria.

<u>Military documentation format</u>	<u>Example PIN under new system</u>	<u>Manufacturing source listing</u>	<u>Document listing</u>
New MIL-H-38534 Standard Microcircuit Drawings	5962-XXXXZZ(H or K)YY	QML-38534	MIL-BUL-103
New MIL-I-38535 Standard Microcircuit Drawings	5962-XXXXZZ(Q or V)YY	QML-38535	MIL-BUL-103
New 1.2.1 of MIL-STD-883 Standard Microcircuit Drawings	5962-XXXXZZ(M)YY	MIL-BUL-103	MIL-BUL-103

6.7 Sources of supply.

6.7.1 Sources of supply for device classes Q and V. Sources of supply for device classes Q and V are listed in QML-38535. The vendors listed in QML-38535 have submitted a certificate of compliance (see 3.6 herein) to DESC-EC and have agreed to this drawing.

6.7.2 Approved sources of supply for device class M. Approved sources of supply for class M are listed in MIL-BUL-103. The vendors listed in MIL-BUL-103 have agreed to this drawing and a certificate of compliance (see 3.6 herein) has been submitted to and accepted by DESC-EC.

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